

Citations for Ion : **Ga**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1962	Bryde, L. Lassen, N. O. Roy-Poulsen, N. O. 'Ranges of Recoil Ions from Alpha-Reactions' <i>Kgl. Danske Videnskab. Selskab Mat. Fys. Medd., 33, No. 8, 1-28 (1962)</i> Comment : R, dR. (0.6-1.3 MeV) Ga, K -> H2, D2, He, Ar, N, Cu; 3.9 MeV F -> N	1962-Bryd
1964	Lassen, N. O. RoyPoulsen, N. O. Sidenius, G. Vistisen, L. 'Stopping of 50 keV Ions in Gases' <i>Kgl. Danske Videnskab. Selskab Mat. Fys. Medd., 34, No. 5, 1-20 (1964)</i> Comment : R. (50 keV) Na, Ga, Au -> H2, D2, Ne, Ar, He, N2	1964-Lass
1964	Porile, N. T. 'Ranges of Low-Energy Gallium Atoms in Copper and Zinc' <i>Phys. Rev. A, 135, 1115-18 (1964)</i> Comment : R. 70-1000 keV Ga -> Cu, Zn	1964-Pori
1964	Sidenius, G. 'Measurement of dE/dX in Gases with Low Energy Heavy Particles' <i>M. R. C. Mcdowell (Ed.) Atomic Collision Processes, North-Holland, Amsterdam, P.709-16 (1964)</i> Comment : S. (20-50 keV) Cl, Ga, Zr, Sb, Pb, Fe, Ca, Ge, U -> H2	1964-Side
1968	Bowman, W. W. Lanzafame, F. M. Cline, C. K. Yu, Yu-Wen Blann, M. 'Recoil Ranges of 0.2 - 5.2 MeV Ions in Vanadium, Nickel, Iron, Zirconium and Gold.' <i>Phys. Rev., 165, 485-93 (1968)</i> Comment : R, dR. Ion(ZI=12-81, E=0.22-5.2 MeV) -> V, Ni, Zr, Au	1968-Bowm
1968	Bulthuis, K. 'Anomalous Penetration of Ga and in Implanted in Silicon' <i>Phys. Letters A, 27, 193-94 (1968)</i> Comment : R, dR. 56 keV In, Ga -> Si (Cryst.)	1968-Bult
1971	Crowder, B. L. 'The Influence of the Amorphous Phase on Ion Distributions and Annealing Behavior of Group Iii and Group V Ions Implanted into Silicon' <i>J. Electrochem. Soc., 118, 943-52 (1971)</i> Comment : R,dR. (50-300 keV) B, Al Ga, P, As, Sb, Bi -> Si	1971-Crow
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. 'Range Distributions of Implanted Ions in SiO2, Si3N4, and Al2O3' <i>Appl. Phys. Letters, 22, 490-92 (1973)</i> Comment : R, dR. Zn, Ga, As, Se, Cd, Te (140-300 keV) -> SiO2, Si3N4, Al2O3	1973-Chu
1973	Chu, W. K. Crowder, B. L. Mayer, J. W. Ziegler, J. F. 'Ranges and Distributions of Ions Implanted into Dielectrics' <i>B.L. Crowder (Ed): Ion Implantation in Semiconductors and Other Materials. Plenum. N. Y. 225-41 (1973)</i> Comment : R.dR. (140-300 keV) Zn, Ga, As, Se, Cd, Te, Zn -> Si, Si3N4, Al2O3	1973-Chu 2

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1973	Gamo, K. Iwaki, M. Masuda, K. Namba, S. Ishihara, S. 'Enhanced Diffusion and Lattice Location of Indium and Gallium Implanted in Silicon' <i>Jap. J. Appl. Phys.</i> , 12, 735-741 (1973) <i>Comment</i> : R. 45 keV In, Ga ->Si	1973-Gamo
1975	Ambridge, T. Heckingbottom, R. 'Effect of Dual Implants into GaAs' <i>Elec. Letters</i> , 11 (1975) <i>Comment</i> : R. 350 keV Se, Ga ->GaAs	1975-Ambr
1975	Dearnaley, G. Gard, G. A. Temple, W. Wilkins, M. A. 'Depth Distribution of Gallium Ions Implanted into Silicon Crystals' <i>Appl. Phys. Letters</i> , 27, 17-18 (1975). <i>Comment</i> : R, dR. 40 keV 72Ga -> Si (Cryst.)	1975-Dear
1976	Grant, W. A. Dodds, D. Williams, J. S. Christodoulides, C. E. Baragiola, R. A. 'Heavy Ion Ranges in Silicon and Aluminum' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 693-703 (1976)</i> <i>Comment</i> : R. 0.01 < Epsilon < 0.8 Cr, Ni, Ga, As, Br, Mo, Cs, La, Nd, Dy, Ta, Pt, Au, Pb -> Si, Al	1976-Gran
1976	Hirvonen, J. K. Hubler, G. K. 'Application of a High-Resolution Magnetic Spectrometer to Near-Surface Analysis' <i>Meyer, G. Linker and F. Kappeler (Ed.):Ion Beam Surface Layer Analysis, Plenum, N. Y., P. 457-69 (1976)</i> <i>Comment</i> : R, dR. 2-60 keV 209Bi, 60 keV 69Ga -> Si	1976-Hirv
1978	Furuya, T. Nishi, H. Inada, T. Sakurai, T. 'Channeled-Ion Implantation of Group-III and Group-V Ions into Silicon' <i>J. Appl. Phys.</i> , 49, 3918-3921 (1978). <i>Comment</i> : R, dR. 100-300 keV B, P, As, Al, Ga -> Si [111], [110], Random	1978-Furu
1978	Shin, B. K. Ehret, J. E. Park, Y. S. Stefiniw, M. 'Dual Implantation of C+ and Ga+ Ions into GaAs' <i>J. Appl. Phys.</i> , 49, 2988-2990 (1978) <i>Comment</i> : R. 120 keV Ga, 60 keV C -> GaAs	1978-Shin
1979	Santry, D. C. Werner, R. D. Westcott, O. M. 'The Range of 120 keV Ions in Solids' <i>IEEE Trans. Nucl. Sci.</i> , Ns-26, 1331-1334 (1979) <i>Comment</i> : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si	1979-Sant
1984	Behar, M. Beirsack, J. P. Fichtner, P. F. P. Fink, D. Leite-Filho, C. V. 'Range and Range Straggling of 15-350 keV Ga in Amorphous Silicon' <i>Rad. Effects Letters</i> , 85, 117-122(1984) <i>Comment</i> : R, dR. Ga (15-350 keV) -> Si	1984-Beha

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1987	Ingram, D. C. Baker, J. A. Walsh, D. A. Strathman, E. 'Range Distributions of MeV Implants in Silicon - 2' <i>Nucl. Inst. Methods, B21, 460-465 (1987)</i> <i>Comment : R, dR, B, P, Ga (0.4-6.0 MeV) -> Si</i>	1987-Ingr
